



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	2.8Ω @ V _{GS} = 10V	350mA
30 V	3.8Ω @ $V_{GS} = 5V$	300mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

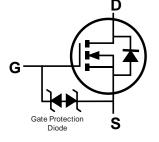
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

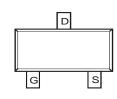
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 <a> § 3
- Weight: 0.008 grams (Approximate)









Top View

Equivalent Circuit

Top View

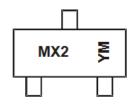
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D8L-7	SOT23	3000/Tape & Reel
DMN63D8L-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \text{MX2} = \text{Product Type Marking Code} \\ \text{YM or } \overline{\text{Y}}\text{M} = \text{Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: B} = 2014) \\ \text{M} = \text{Month (ex: 9} = \text{September)} \end{array}$

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н	- 1	J	K	L	М
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
								3				



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	30	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Prain Compart (Note C) // 40)/	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	350 280	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	400 310	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I _{DM}	1.2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	359	°C/W
Total Power Dissipation (Note 6)		P _D	520	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	243	°C/W
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C

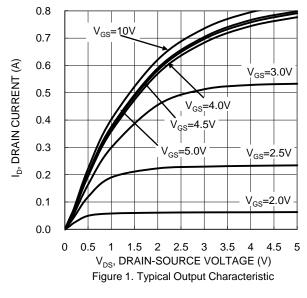
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

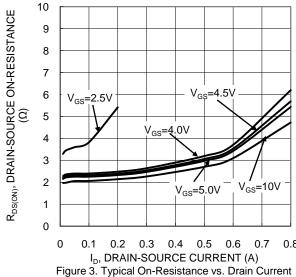
01 110			-		11.14	T (0 10)
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			ı	1		I
Drain-Source Breakdown Voltage	BV _{DSS}	30		_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μΑ	$V_{DS} = 30V$, $V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	_	—	±10.0	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.8		1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
				2.8		$V_{GS} = 10.0V, I_D = 250mA$
		_	_	3.8		$V_{GS} = 5.0V, I_D = 250mA$
Static Drain-Source On-Resistance	R _{DS(ON)}			4.2	Ω	$V_{GS} = 4.5V, I_D = 250mA$
		_	_	4.5		$V_{GS} = 4.0V, I_D = 250mA$
		_	_	13		$V_{GS} = 2.5V, I_D = 10mA$
Forward Transconductance	g FS	80		_	mS	V _{DS} = 10V, I _D = 0.115A
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	23.2	_		
Output Capacitance	Coss	_	3.0	_	рF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	2.2	_		
Gate Resistance	R _G	_	79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge V _{GS} = 10V	Q_g	_	0.9	_		
Total Gate Charge V _{GS} = 4.5V	Qg	_	0.4	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$
Gate-Source Charge	Q _{gs}	_	0.1	_	IIC	$I_D = 150 \text{mA}$
Gate-Drain Charge	Q_{gd}	_	0.2	_		
Turn-On Delay Time	t _{D(ON)}		2.3	_		
Turn-On Rise Time	t _R	_	3.9	_		$V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V$
Turn-Off Delay Time	t _{D(OFF)}		11.4	_	ns	$R_{GEN} = 25\Omega$
Turn-Off Fall Time	t _F	_	16.7	_		

5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

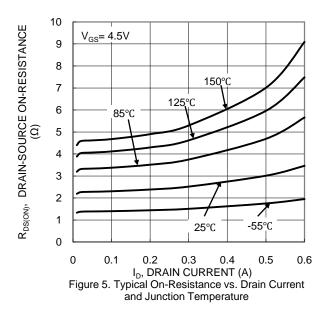
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

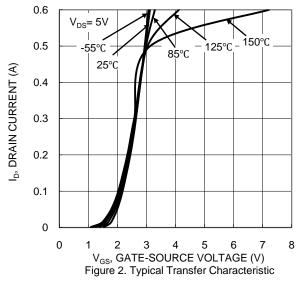


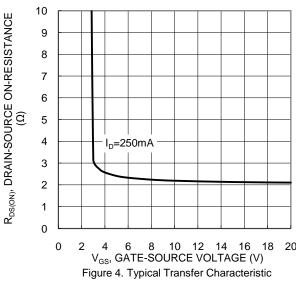




and Gate Voltage







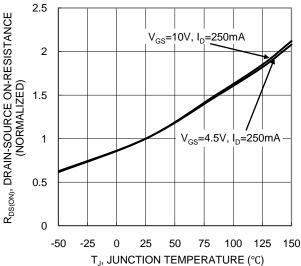


Figure 6. On-Resistance Variation with Junction Temperature



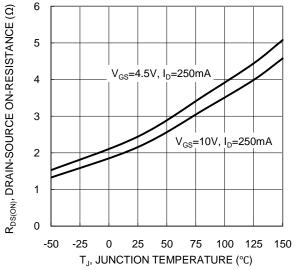
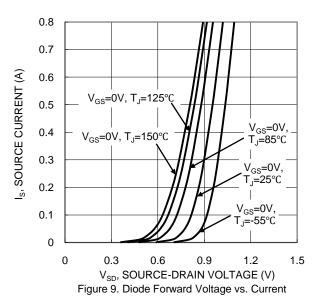
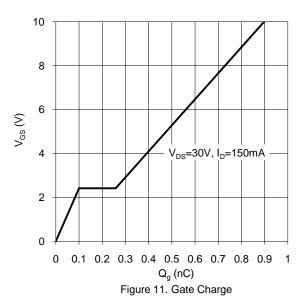
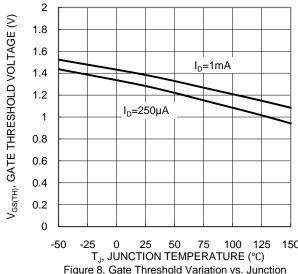
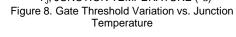


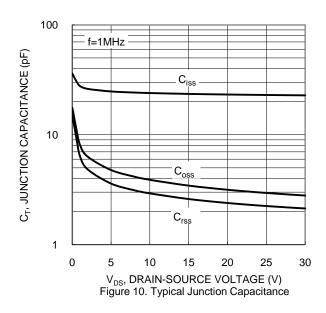
Figure 7. On-Resistance Variation with Junction Temperature

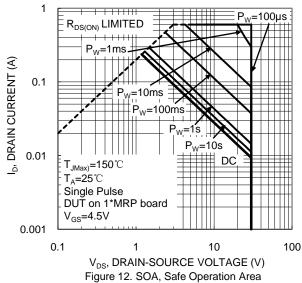




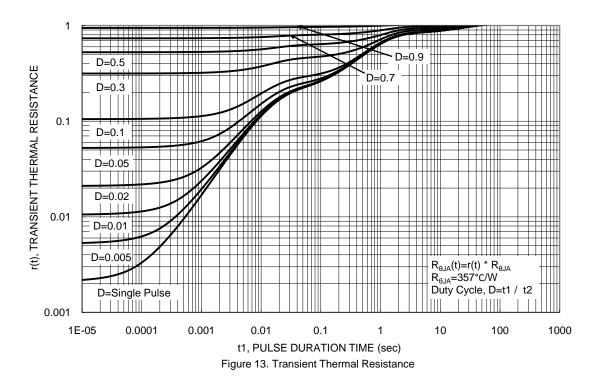






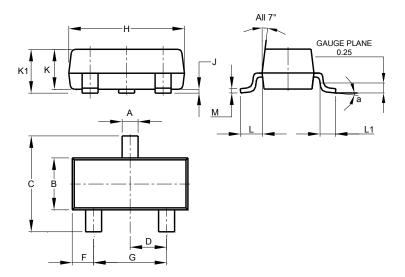






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

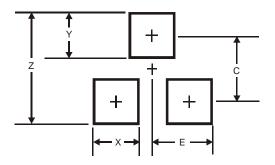


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45 0.61 0.55							
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а		8°						
All	All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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